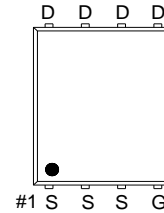
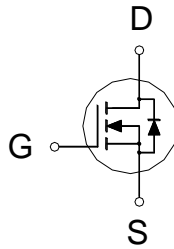




**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
110V	16mΩ	36A



G. GATE  
D. DRAIN  
S. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ °C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	110	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current <sup>3</sup>	$T_C = 25\text{ °C}$	$I_D$	36	A
	$T_C = 100\text{ °C}$		23	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	100	
Continuous Drain Current	$T_A = 25\text{ °C}$	$I_D$	11	
	$T_A = 70\text{ °C}$		8.8	
Avalanche Current		$I_{AS}$	13.5	
Avalanche Energy	$L = 1\text{mH}$	$E_{AS}$	91	mJ
Power Dissipation	$T_C = 25\text{ °C}$	$P_D$	50	W
	$T_C = 100\text{ °C}$		20	
Power Dissipation <sup>4</sup>	$T_A = 25\text{ °C}$	$P_D$	4.4	W
	$T_A = 70\text{ °C}$		2.8	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$		28	°C / W
Junction-to-Ambient <sup>2</sup>	Steady-State	$R_{\theta JA}$		54	
Junction-to-Case	Steady-State	$R_{\theta JC}$		2.5	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25\text{ °C}$ .

<sup>3</sup>Package limitation current is 25A.

<sup>4</sup>The Power dissipation is based on  $R_{\theta JA} t \leq 10\text{s}$  value.

**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)**

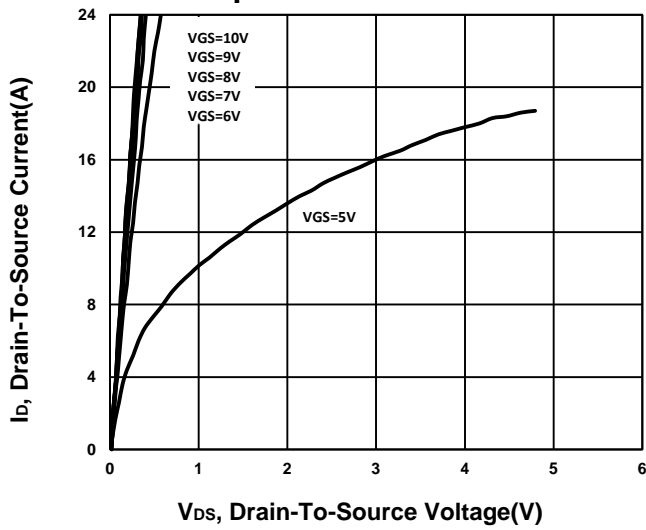
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	110			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 88V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55 °C			10	
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DSON</sub>	V <sub>GS</sub> = 7V, I <sub>D</sub> = 11A		14	21	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A		13	16	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 11A		45		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		3017		pF
Output Capacitance	C <sub>oss</sub>			255		
Reverse Transfer Capacitance	C <sub>rss</sub>			152		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz		1		Ω
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10V	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A	58		nC
		V <sub>GS</sub> = 7V		44		
Gate-Source Charge <sup>2</sup>	Q <sub>gs</sub>	16.5				
Gate-Drain Charge <sup>2</sup>	Q <sub>gd</sub>	21.5				
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 55V, I <sub>D</sub> ≅ 11A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 6Ω		35		
Rise Time <sup>2</sup>	t <sub>r</sub>		90			
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>		78			
Fall Time <sup>2</sup>	t <sub>f</sub>		56			
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)</b>						
Continuous Current <sup>3</sup>	I <sub>S</sub>				41	A
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 11A, V <sub>GS</sub> = 0V			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 11A, di <sub>F</sub> /dt = 100A / μS		36		nS
Reverse Recovery Charge	Q <sub>rr</sub>			41		nC

<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

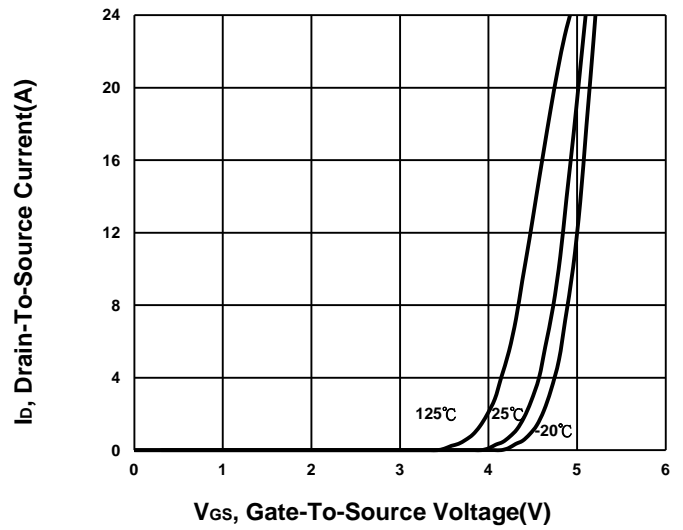
<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Package limitation current is 25A.

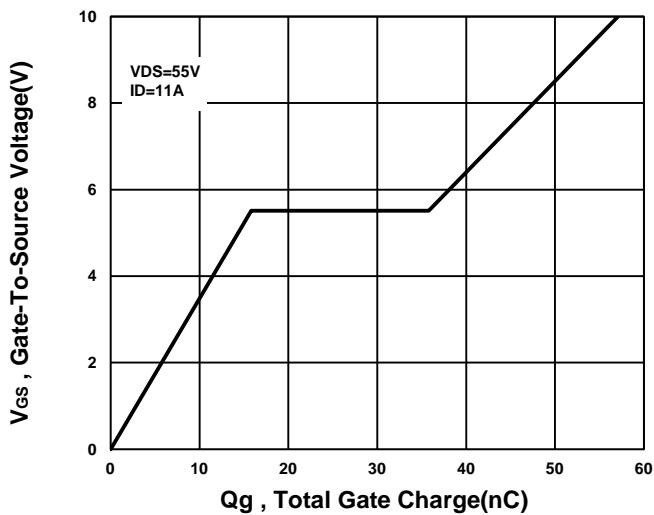
**Output Characteristics**



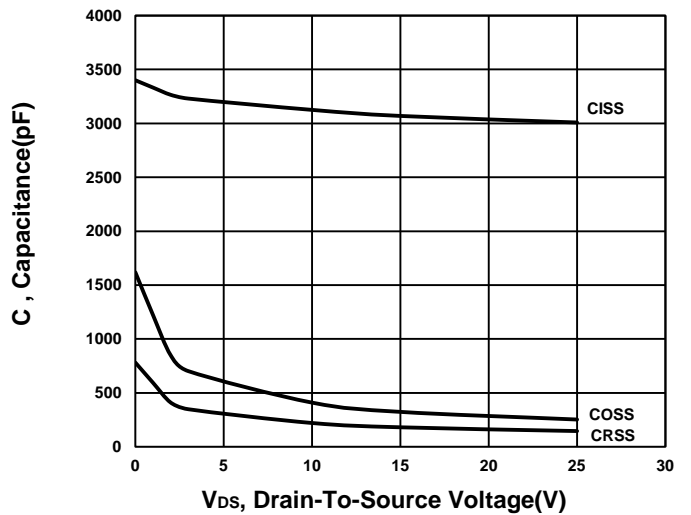
**Transfer Characteristics**



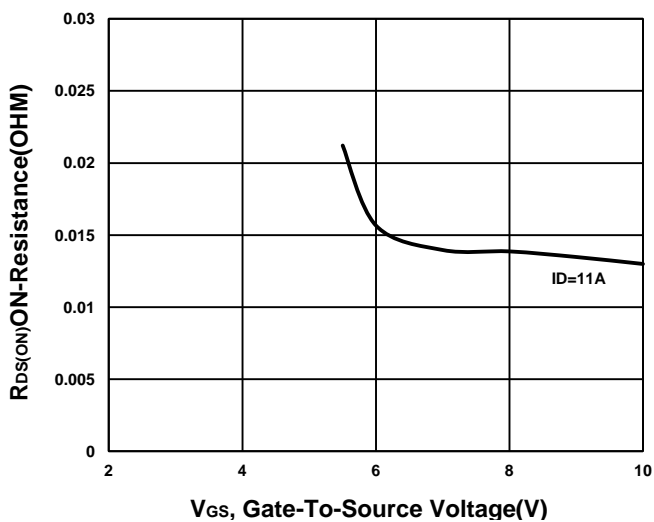
**Gate charge Characteristics**



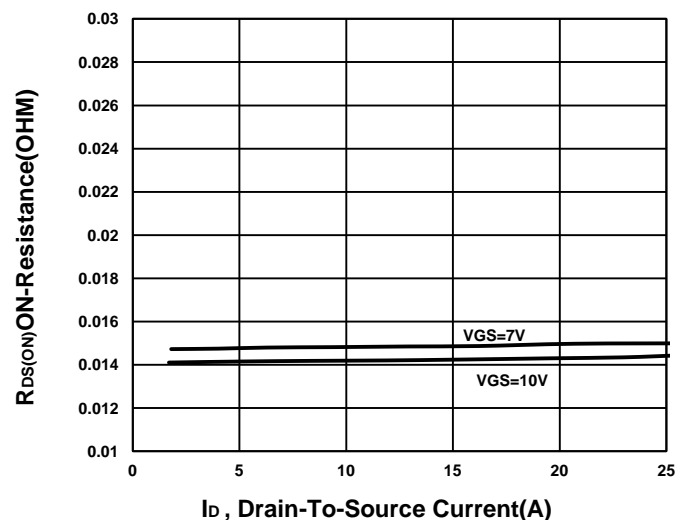
**Capacitance Characteristic**



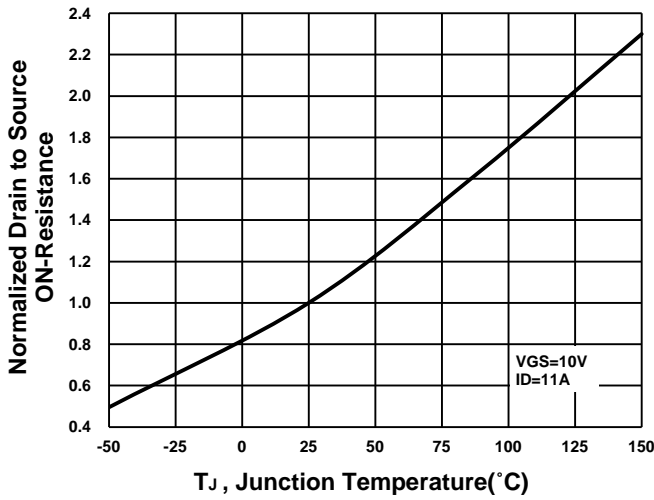
**On-Resistance VS Gate-To-Source**



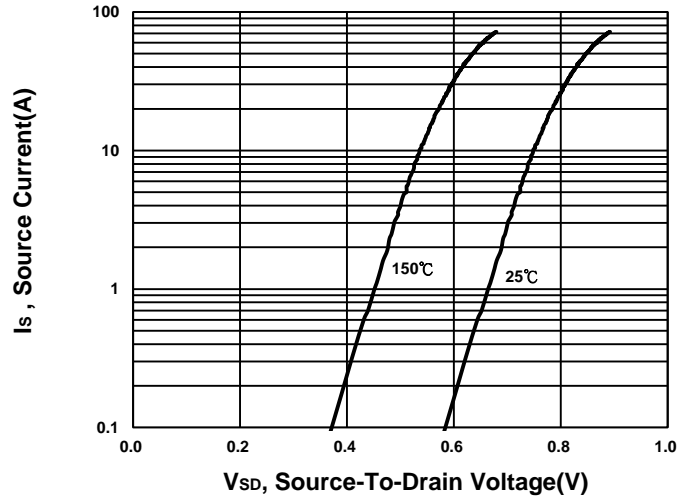
**On-Resistance VS Drain Current**



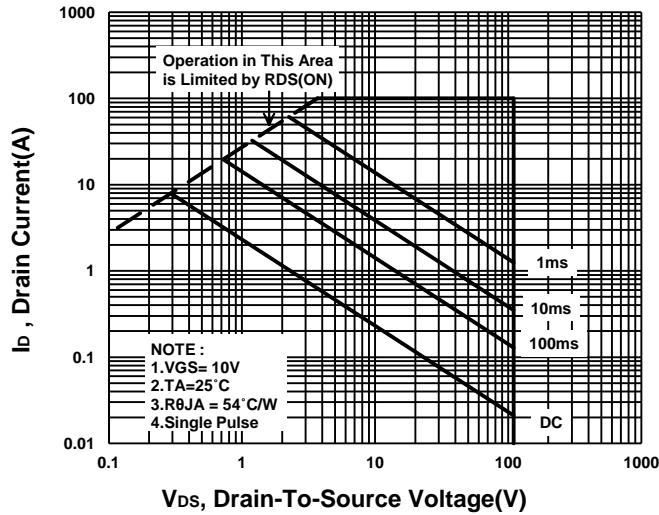
**On-Resistance VS Temperature**



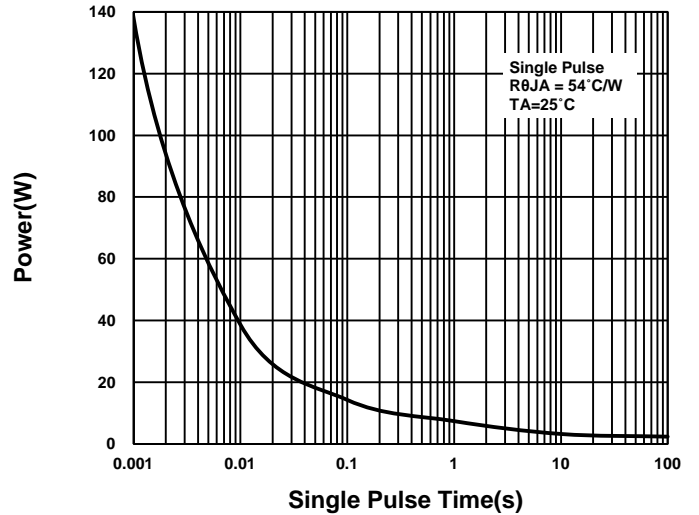
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

